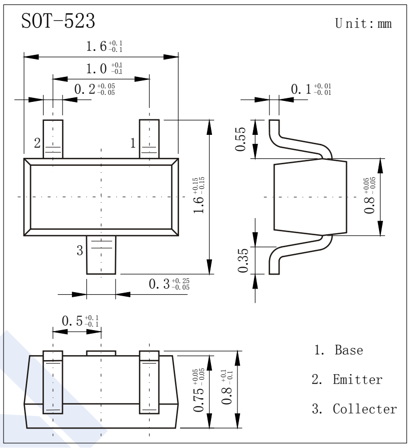
PNP Transistors
KX2001P

■ Features

- ● High Voltage Transistors
- ● Pb-Free Packages are Available



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-200	V
Collector - Emitter Voltage	V_{CEO}	-180	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-0.2	A
Collector Power Dissipation	P_C	0.15	W
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA， I_E=0	-200			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA， I_B=0	-180			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A， I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -120V , I_E=0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB}= -4V , I_C=0			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-50 mA, I_B=-5mA			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C= -50 mA, I_B=- 5mA			-1.0	
DC current gain	$h_{FE(1)}$	V_{CE}= -5V, I_C= -10mA	100		250	
Transition frequency	f_T	V_{CE}= -5V, I_C= -10mA,f=30MHz	100		300	MHz

* Pulse Test: Pulse Width = 300 μ s, Duty Cycle=2.0%.

■ Classification of hfe

Marking	21P
Range	100−250